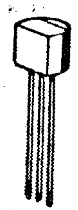
MICRO ELECTRONICS

2N5232

NPN SILICON TRANSISTOR

TO-92B



ECB

2N5232 is NPN silicon planar transistor use in general purpose applications.

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	50V
Collector-Base Voltage	VCBO	70V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	100mA
Total Power Dissipation	Ptot	330mW
Operating Junction & Storage Temperature	Tj,Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO	50		V	IC=10mA IB=0
Collector-Base Breakdown Voltage	BVCBO	70		V	IC=100μA IE=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=100μA IC=0
Collector Cutoff Current	ICBO		30	nA	VCB=50V IE=0
Collector Cutoff Current	ICES		30	nA	VCB=50V VEB=0
Emitter Cutoff Current	IEBO		50	nA	VEB=5V IC=0
D.C. Current Gain	HFE	250	500		IC=2mA VCE=10V
Base-Emitter Voltage	VBE		0.9	V	IC=2mA VCE=10V
Collector-Emitter Saturation Voltage	VCE(sat)		0.12	V	IC=10mA IB=1mA
Base-Emitter Saturation Voltage	VBE(sat)		0.78	V	IC=10mA IB=1mA
Output Capacitance	Cob		4	pF	VCB=10V f=1MHz

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